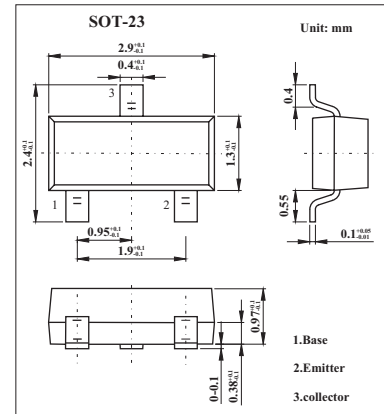


## High Voltage Transistor

### FMMT458

#### ■ Features

- 400 Volt  $V_{CE0}$



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	400	V
Collector-emitter voltage	$V_{CE0}$	400	V
Emitter-base voltage	$V_{EB0}$	5	V
Peak collector current	$I_{CM}$	1	A
Collector current	$I_C$	225	mA
Base current	$I_B$	200	mA
Power dissipation	$P_{tot}$	500	mW
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	$^\circ\text{C}$



炬芯微  
XUANXINWEI

SMD Type

Transistors

## FMMT458

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A$	400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A$	5			V
Collector cutoff current	$I_{CBO}$	$V_{CB}=320V$			100	nA
Collector Cut-Off Current	$I_{CES}$	$V_{CE}=320V$			100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4V$			100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=20mA, I_B=2mA$			0.2	V
		$I_C=50mA, I_B=6mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=5mA$			0.9	V
Base-emitter turn on voltage	$V_{BE(on)}$	$I_C=50mA, V_{CE}=10V$			0.9	V
Static Forward Current Transfer Ratio	$h_{FE}$	$I_C=1mA, V_{CE}=10V$	100			
		$I_C=50mA, V_{CE}=10V^*$	100		300	
		$I_C=100mA, V_{CE}=10V^*$	15			
Transition frequency	$f_T$	$I_C=10mA, V_{CE}=20V, f=20MHz$	50			MHz
Output capacitance	$C_{obo}$	$V_{CB}=20V, f=1MHz$			5	pF
Switching times	$t_{on}$	$I_C=50mA, V_{CC}=100V$		135		ns
	$t_{off}$	$I_{B1}=5mA, I_{B2}=-10mA$		2260		ns

### ■ Marking

Marking	458
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